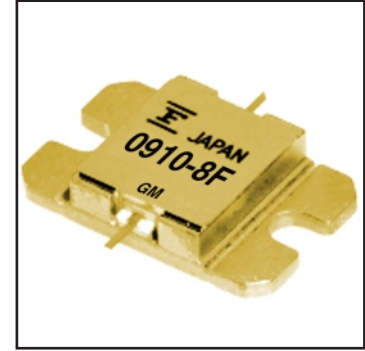


FEATURES

- High Output Power: $P_{1dB} = 39.0dBm$ (Typ.)
- High Gain: $G_{1dB} = 7.5dB$ (Typ.)
- High PAE: $\eta_{add} = 29%$ (Typ.)
- Low $IM_3 = -46dBc @ P_o = 28.5dBm$
- Broad Band: 9.5 ~ 10.5GHz
- Impedance Matched $Z_{in}/Z_{out} = 50\Omega$



DESCRIPTION

The FLM0910-8F is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.

Fujitsu's stringent Quality Assurance Program assures the highest reliability and consistent performance.

ABSOLUTE MAXIMUM RATING (Ambient Temperature $T_a=25^\circ C$)

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	V_{DS}		15	V
Gate-Source Voltage	V_{GS}		-5	V
Total Power Dissipation	P_T	$T_c = 25^\circ C$	42.8	W
Storage Temperature	T_{stg}		-65 to +175	$^\circ C$
Channel Temperature	T_{ch}		175	$^\circ C$

Fujitsu recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage (V_{DS}) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 32.0 and -4.4 mA respectively with gate resistance of 100 Ω .

ELECTRICAL CHARACTERISTICS (Ambient Temperature $T_a=25^\circ C$)

Item	Symbol	Test Conditions	Limit			Unit	
			Min.	Typ.	Max.		
Saturated Drain Current	I_{DSS}	$V_{DS} = 5V, V_{GS} = 0V$	-	3400	5200	mA	
Transconductance	g_m	$V_{DS} = 5V, I_{DS} = 2200mA$	-	3400	-	mS	
Pinch-off Voltage	V_p	$V_{DS} = 5V, I_{DS} = 170mA$	-0.5	-1.5	-3.0	V	
Gate Source Breakdown Voltage	V_{GSO}	$I_{GS} = -170\mu A$	-5.0	-	-	V	
Output Power at 1dB G.C.P.	P_{1dB}	$V_{DS} = 10V,$ $I_{DS} = 0.65 I_{DSS}$ (Typ.), $f = 9.5 \sim 10.5$ GHz, $Z_S = Z_L = 50$ ohm	38.5	39.0	-	dBm	
Power Gain at 1dB G.C.P.	G_{1dB}		6.5	7.5	-	dB	
Drain Current	I_{dsr}		-	2200	2600	mA	
Power-added Efficiency	η_{add}		-	29	-	%	
Gain Flatness	ΔG		-	-	± 0.6	dB	
3rd Order Intermodulation Distortion	IM_3		$f = 10.5$ GHz, $\Delta f = 10$ MHz 2-Tone Test $P_{out} = 28.5dBm$ S.C.L.	-44	-46	-	dBc
Thermal Resistance	R_{th}		Channel to Case	-	3.0	3.5	$^\circ C/W$
Channel Temperature Rise	ΔT_{ch}	$10V \times I_{dsr} \times R_{th}$	-	-	80	$^\circ C$	

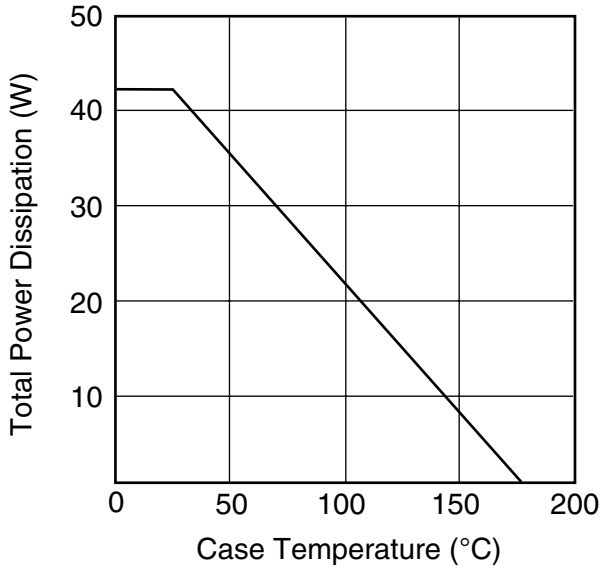
CASE STYLE: IB

G.C.P.: Gain Compression Point, S.C.L.: Single Carrier Level

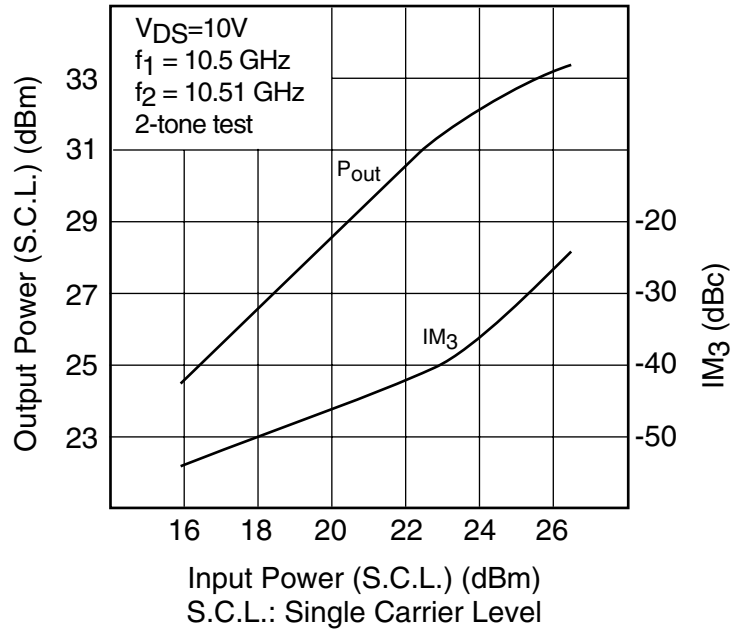
FLM0910-8F

X, Ku-Band Internally Matched FET

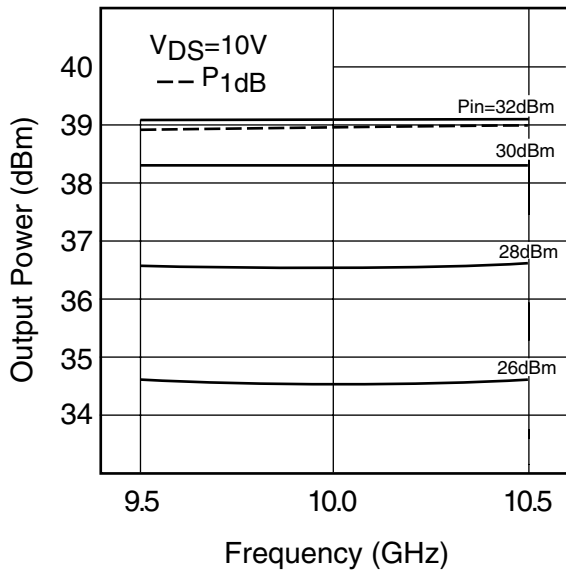
POWER DERATING CURVE



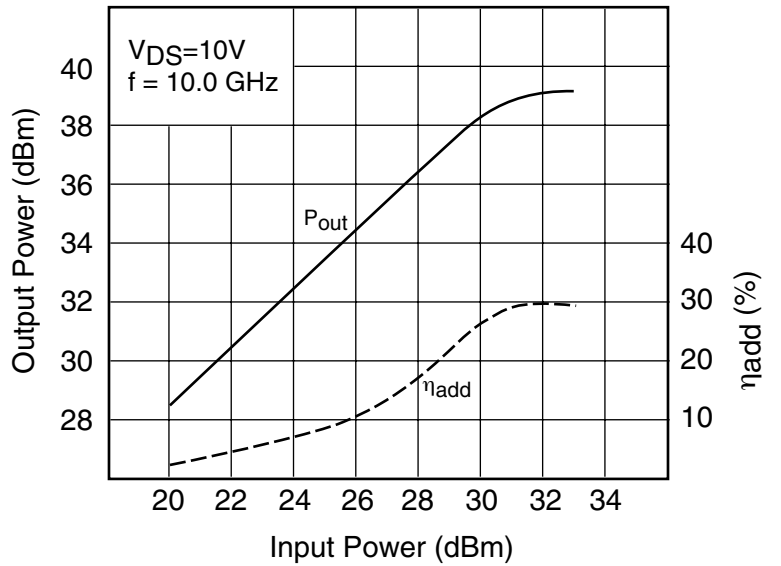
OUTPUT POWER & IM₃ vs. INPUT POWER

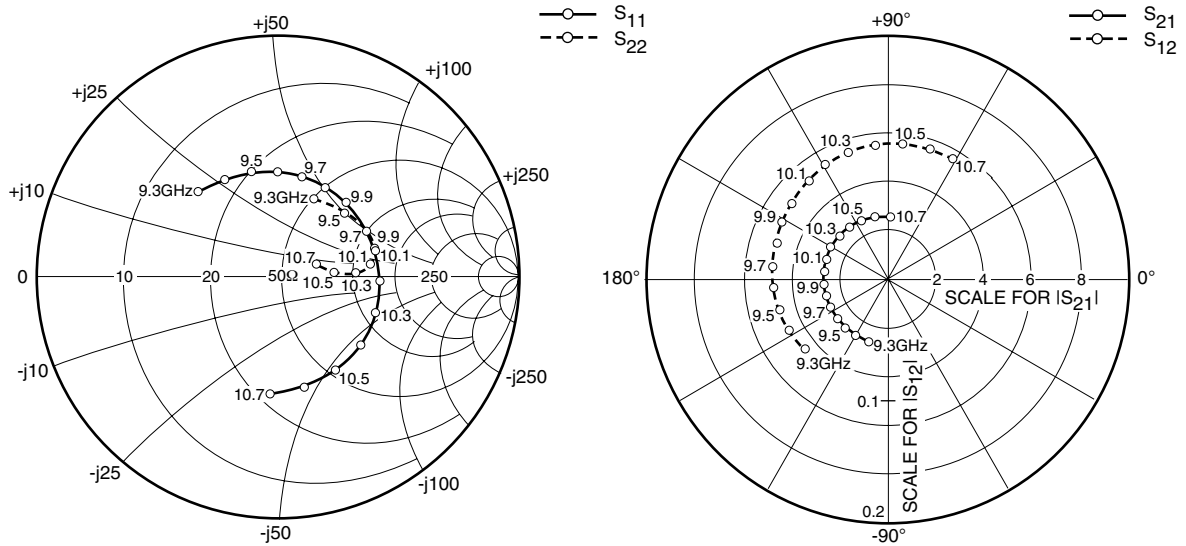


OUTPUT POWER vs. FREQUENCY



OUTPUT POWER vs. INPUT POWER





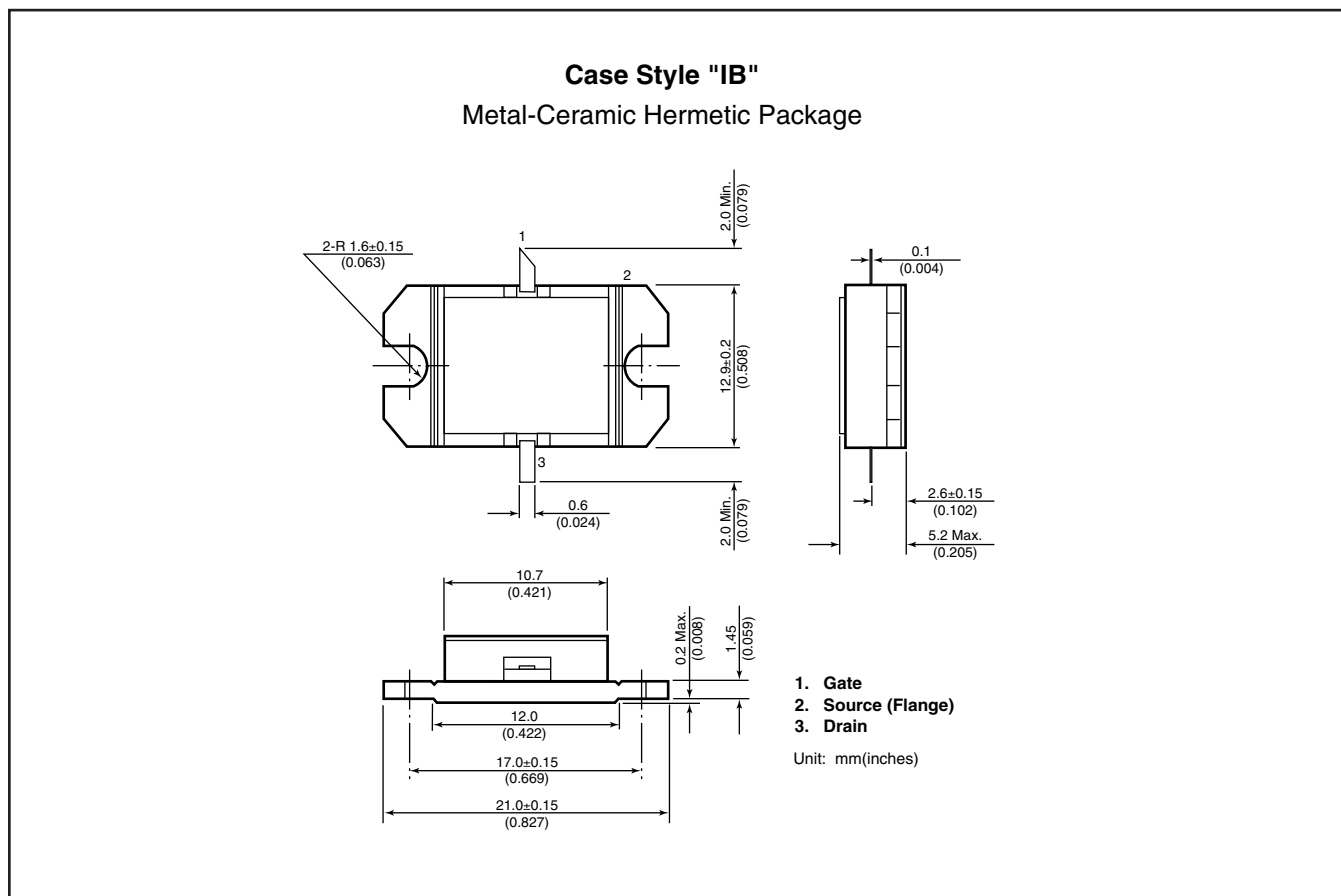
S-PARAMETERS

$V_{DS} = 10V, I_{DS} = 2200mA$

FREQUENCY (MHZ)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
9300	.489	132.9	2.699	-108.2	.090	-140.2	.352	66.0
9400	.464	118.8	2.686	-120.0	.092	-152.4	.364	54.7
9500	.451	104.4	2.692	-131.6	.093	-164.8	.377	44.2
9600	.438	90.5	2.657	-142.5	.095	-175.1	.397	35.3
9700	.428	76.7	2.642	-153.9	.096	174.3	.412	28.2
9800	.421	62.4	2.640	-164.8	.095	162.4	.421	21.9
9900	.420	48.0	2.637	-175.5	.100	151.7	.417	17.2
10000	.418	32.1	2.651	173.5	.101	142.3	.406	12.1
10100	.420	15.7	2.668	162.3	.104	130.3	.385	7.9
10200	.424	-2.0	2.689	150.9	.107	119.4	.358	5.2
10300	.428	-20.4	2.703	138.8	.109	108.0	.320	2.6
10400	.440	-39.3	2.703	126.7	.108	96.1	.276	2.6
10500	.452	-58.2	2.691	114.2	.112	84.3	.231	3.3
10600	.469	-76.6	2.656	101.7	.112	72.3	.194	8.4
10700	.484	-94.2	2.600	89.0	.111	61.1	.166	17.4

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X, Ku-Band Internally Matched FET



For further information please contact:

FUJITSU COMPOUND SEMICONDUCTOR, INC.

2355 Zanker Rd.
San Jose, CA 95131-1138, U.S.A.
Phone: (408) 232-9500
FAX: (408) 428-9111
www.fcsi.fujitsu.com

FUJITSU MICROELECTRONICS, LTD.

Compound Semiconductor Division
Network House
Norreys Drive
Maidenhead, Berkshire SL6 4FJ
Phone: +44 (0)1628 504800
FAX: +44 (0)1628 504888

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- Do not put these products into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.

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